

Technical Data Sheet

ACS Material Single Layer Graphene Oxide Powder (H Method)

Table of Contents

- 1 Preparation Method
- 2 Characterizations
- 3 Application Fields

Contact Information:

Manufacturer: ACS Material, LLC. Address: 959 E Walnut St., Suite 100 Pasadena, CA 91106, USA

> Phone: (866)-227-0656 Fax: (781)-518-0284

E-Mail: contact@acsmaterial.com

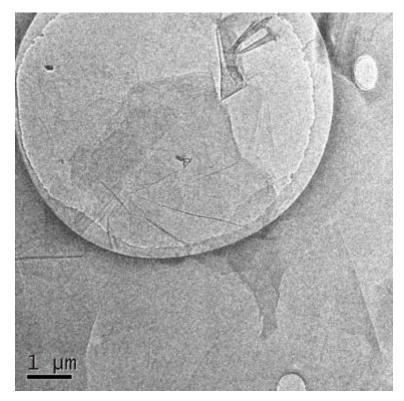
Revision: 092617

1. Preparation Method

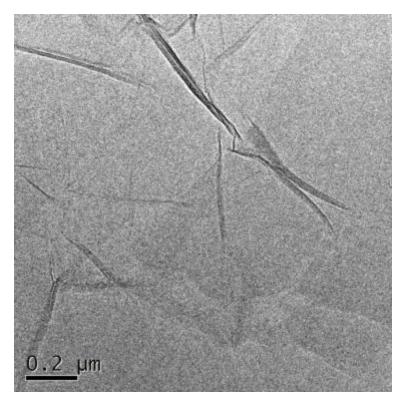
Hummer's Method

2. Characterizations

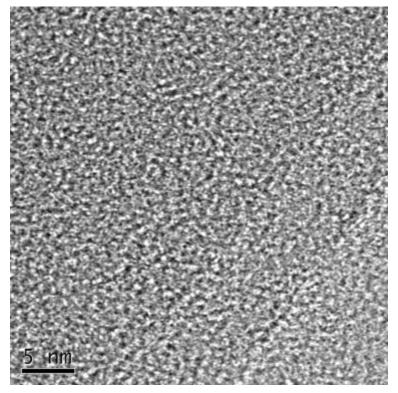
Appearance:	Brown powder	
Purity:	~ 99%	
Lateral size:	0.5-5 μm	
Thickness:	0.8-1.2 nm	
Singer layer Ratio:	~ 99%	



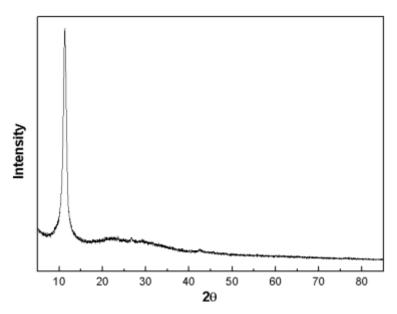
Typical TEM Image (1) of ACS Material Single Layer Graphene Oxide Powder (H Method)



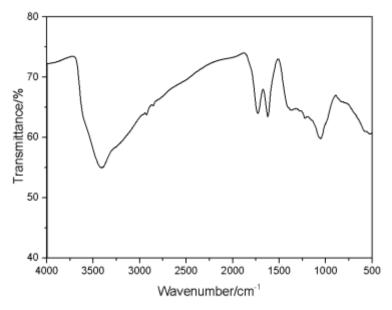
Typical TEM Image (2) of ACS Material Single Layer Graphene Oxide Powder (H Method)



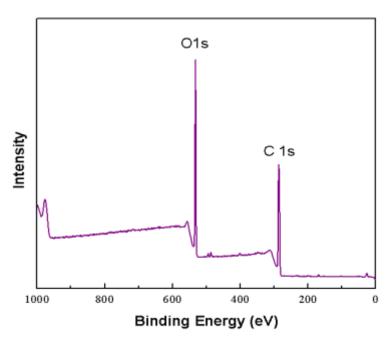
Typical TEM Image (3) of ACS Material Single Layer Graphene Oxide Powder (H Method)



XRD Analysis of ACS Material Single Layer Graphene Oxide Powder (H Method)



IR Pattern of ACS Material Single Layer Graphene Oxide Powder (H Method)



XPS Spectrum of ACS Material Single Layer Graphene Oxide Powder (H Method)

XPS Peak Table of ACS Material Single Layer Graphene Oxide Powder (H Method)

Name	Peak BE	FWHM eV	Area(P)CPS.eV	Atomic %
C1s	286.87	1.41	75584.6	66.91
O1s	532.55	1.81	98969.68	33.09

3. Application Fields

Graphene and polymers manufacture, water purification, flexible rechargeable battery electrode, optically transparent films, papers, sensors, nanocarriers for metal catalysis, anti-electrostatic additives, adsorption material and biomedicine *etc*.

Disclaimer: ACS Material, LLC believes that the information in this Technical Data Sheet is accurate and represents the best and most current information available to us. ACS Material makes no representations or warranties either express or implied, regarding the suitability of the material for any purpose or the accuracy of the information contained within this document. Accordingly, ACS Material will not be responsible for damages resulting from use of or reliance upon this information.